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September 2014

FDZ1323NZ

Common Drain N-Channel 2.5 V PowerTrench® WL-CSP MOSFET 20 V, 10 A, 13 m Ω

Features

- Max $r_{S1S2(on)} = 13 \text{ m}\Omega$ at $V_{GS} = 4.5 \text{ V}$, $I_{S1S2} = 1 \text{ A}$
- Max $r_{S1S2(on)} = 13 \text{ m}\Omega$ at $V_{GS} = 3.8 \text{ V}$, $I_{S1S2} = 1 \text{ A}$
- Max $r_{S1S2(on)} = 16 \text{ m}\Omega$ at $V_{GS} = 3.1 \text{ V}$, $I_{S1S2} = 1 \text{ A}$
- Max $r_{S1S2(on)} = 18 \text{ m}\Omega$ at $V_{GS} = 2.5 \text{ V}$, $I_{S1S2} = 1 \text{ A}$
- Occupies only 3 mm² of PCB area
- Ultra-thin package: less than 0.35 mm height when mounted to PCB
- High power and current handling capability
- HBM ESD protection level > 3.6 kV (Note 3)
- RoHS Compliant

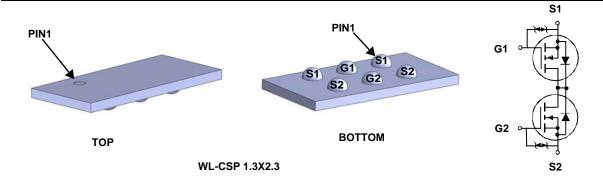


General Description

This device is designed specifically as a single package solution for Li-lon battery pack protection circuit and other ultra-portable applications. It features two common drain N-channel MOSFETs, which enables bidirectional current flow, on Fairchild's advanced PowerTrench® process with state of the art "low pitch" WLCSP packaging process, the FDZ1323NZ minimizes both PCB space and $r_{\rm S1S2(on)}.$ This advanced WLCSP MOSFET embodies a breakthrough in packaging technology which enables the device to combine excellent thermal transfer characteristics, ultra-low profile packaging, low gate charge and low $r_{\rm S1S2(on)}.$

Applications

- Battery management
- Load switch
- Battery protection



MOSFET Maximum Ratings T_A = 25°C unless otherwise noted

Symbol	Parameter			Ratings	Units
V _{S1S2}	Source1 to Source2 Voltage			20	V
V_{GS}	Gate to Source Voltage			±12	V
	Source1 to Source2 Current -Continuous	T _A = 25°C	(Note 1a)	10	۸
IS1S2	-Pulsed		40	Α	
Б	Power Dissipation	T _A = 25°C	(Note 1a)	2	W
P_{D}	Power Dissipation	T _A = 25°C	(Note 1b)	0.5	VV
T _J , T _{STG}	Operating and Storage Junction Temperature Range			-55 to +150	°C

Thermal Characteristics

$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	(Note 1a)	62	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	(Note 1b)	257	C/VV

Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
EC	FDZ1323NZ	WL-CSP 1.3X2.3	7 "	8 mm	5000 units

Electrical Characteristics T_J = 25 °C unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Тур	Max	Units
Off Characteristics						
I _{S1S2}	Zero Gate Voltage Source1 to Source2 Current	V _{S1S2} = 16 V, V _{GS} = 0 V			1	μА
I _{GSS}	Gate to Source Leakage Current	$V_{GS} = \pm 12 \text{ V}, V_{S1S2} = 0 \text{ V}$			±10	μΑ

On Characteristics

V _{GS(th)}	Gate to Source Threshold Voltage	$V_{GS} = V_{S1S2}, I_{S1S2} = 250 \mu A$	0.4	0.9	1.2	V
-	$V_{GS} = 4.5 \text{ V}, I_{S1S2} = 1 \text{ A}$	4.5	9.7	13		
		$V_{GS} = 3.8 \text{ V}, I_{S1S2} = 1 \text{ A}$	5.5	10	13	
r _{S1S2(on)}	1.55(4)	V _{GS} = 3.1 V, I _{S1S2} = 1 A	7	11	16	$m\Omega$
		V _{GS} = 2.5 V, I _{S1S2} = 1 A	8	13	18	
		$V_{GS} = 4.5 \text{ V}, I_{S1S2} = 1 \text{ A}, T_J = 125 ^{\circ}\text{C}$		13	20	
g _{FS}	Forward Transconductance	V _{S1S2} = 5 V, I _{S1S2} = 1 A		9		S

Dynamic Characteristics

C _{iss}	Input Capacitance	V 10 V V 0 V	1545	2055	pF
C _{oss}	Output Capacitance	V _{S1S2} = 10 V, V _{GS} = 0 V, f = 1 MHz	269	405	pF
C _{rss}	Reverse Transfer Capacitance	1 - 1 101112	252	380	pF

Switching Characteristics

t _{d(on)}	Turn-On Delay Time		12	22	ns
t _r	Rise Time	V _{S1S2} = 10 V, I _{S1S2} = 1 A,	13	23	ns
t _{d(off)}	Turn-Off Delay Time	$V_{GS} = 4.5 \text{ V}, R_{GEN} = 6 \Omega$	34	54	ns
t _f	Fall Time		13	23	ns
Q _q	Total Gate Charge		17	24	nC
Q_{gs}	Gate to Source1 Gate Charge	$V_{S1S2} = 10 \text{ V}, I_{S1S2} = 1 \text{ A},$ $V_{G1S1} = 4.5 \text{ V}, V_{G2S2} = 0 \text{ V}$	1.9		nC
Q_{gd}	Gate to Source2 "Miller" Charge	VG1S1 = 4.5 V, VG2S2 = 0 V	5.4		nC

Source1 to Source2 Diode Characteristics

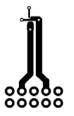
I _{fss}	Maximum Continuous Source1 to Source2 Diode Forward Current				1	Α
V _{fss}	Source1 to Source2 Diode Forward Voltage	$V_{G1S1} = 0 \text{ V, } V_{G2S}$ $I_{fss} = 1 \text{ A}$	₂ = 4.5 V, (Note 2)	0.6	1.2	V

Notes:

1. R_{BJA} is determined with the device mounted on a 1 in² pad 2 oz copper pad on a 1.5 x 1.5 in. board of FR-4 material. R_{BJC} is guaranteed by design while R_{BCA} is determined by the user's board design.



a. 62 °C/W when mounted on a 1 in² pad of 2 oz copper.



 b. 257 °C/W when mounted on a minimum pad of 2 oz copper.

- 2. Pulse Test: Pulse Width < 300 us, Duty cycle < 2.0%.
- 3. The diode connected between the gate and source serves only protection against ESD. No gate overvoltage rating is implied.

Typical Characteristics T_J = 25°C unless otherwise noted

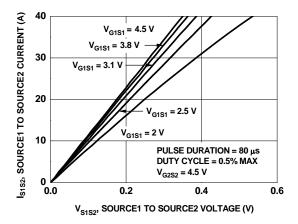


Figure 1. On-Region Characteristics

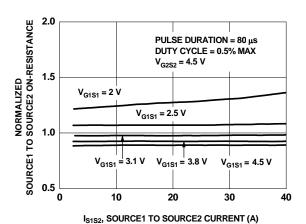


Figure 3. Normalized On-Resistance vs Source1 to Source2 Current and Gate Voltage

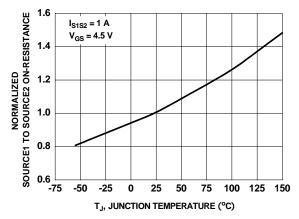


Figure 5. Normalized On Resistance vs Junction Temperature

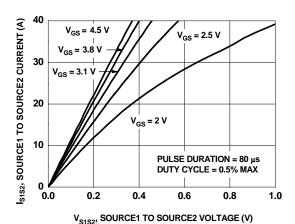


Figure 2. On-Region Characteristics

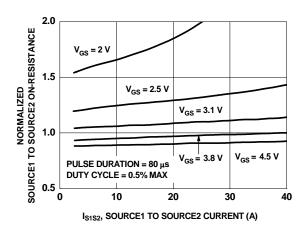


Figure 4. Normalized On-Resistance vs Source1 to Source2 Current and Gate Voltage

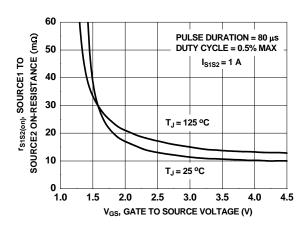


Figure 6. On Resistance vs Gate to Source Voltage

Typical Characteristics $T_J = 25^{\circ}C$ unless otherwise noted

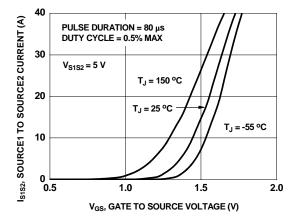


Figure 7. Transfer Characteristics

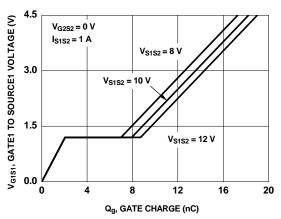


Figure 9. Gate Charge Characteristics

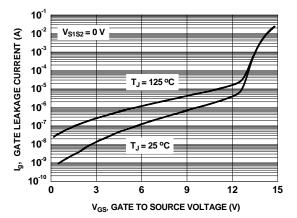
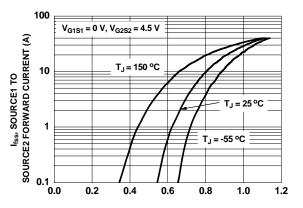


Figure 11. Gate Leakage Current vs Gate to Source Voltage



V_{fss}, BODY DIODE FORWARD VOLTAGE (V)

Figure 8. Source1 to Source2 Diode Forward Voltage vs Source Current

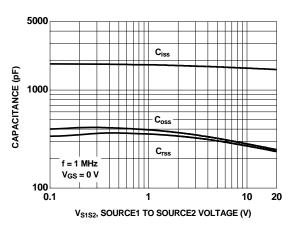
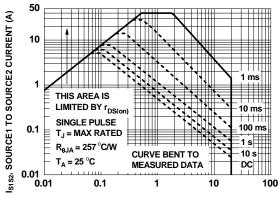


Figure 10. Capacitance vs Source1 to Source2 Voltage



V_{S1S2}, SOURCE1 TO SOURCE2 VOLTAGE (V)

Figure 12. Forward Bias Safe Operating Area



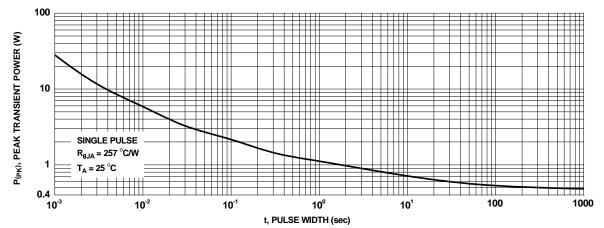


Figure 13. Single Pulse Maximum Power Dissipation

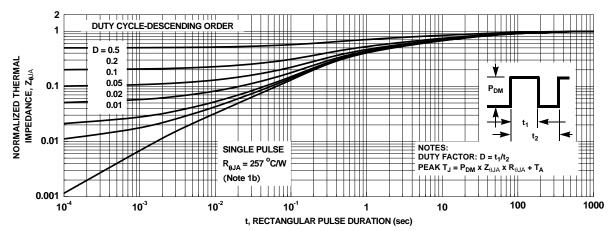
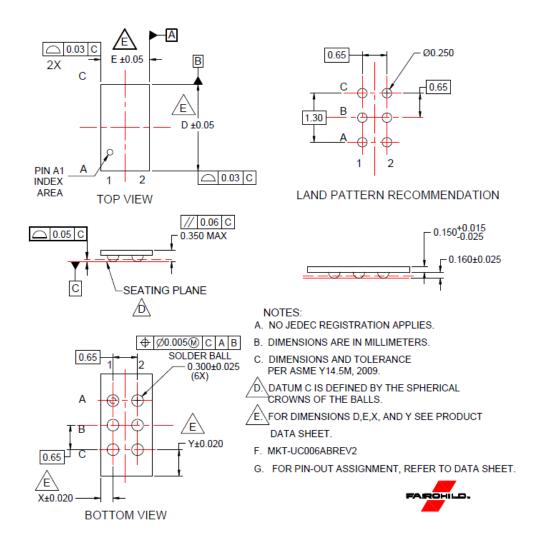


Figure 14. Junction-to-Ambient Transient Thermal Response Curve

Dimensional Outline and Pad Layout



Pin Definations:

Gate	Source1	Source2
B1, B2	A1, C1	A2, C2

Product Specific Dimensions:

D	E X		Υ	
2.3 mm	1.3 mm	0.315 mm	0.49 mm	

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